

NTMFS5844NL, NVMFS5844NL

MOSFET – Power, Single, N-Channel 60 V, 61 A, 12 mΩ



ON Semiconductor®

<http://onsemi.com>

Features

- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- NVMFS5844NLWF – Wettable Flanks Product
- NVMFS Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DS}	60	V
Gate-to-Source Voltage			V_{GS}	± 20	V
Continuous Drain Current $R_{\psi J-mb}$ (Notes 1, 2, 3, 4)	Steady State	$T_{mb} = 25^\circ\text{C}$	I_D	61	A
		$T_{mb} = 100^\circ\text{C}$		43	
		$T_{mb} = 25^\circ\text{C}$	P_D	107	W
		$T_{mb} = 100^\circ\text{C}$		54	
Power Dissipation $R_{\psi J-mb}$ (Notes 1, 2, 3)	Steady State	$T_A = 25^\circ\text{C}$	I_D	11.2	A
		$T_A = 100^\circ\text{C}$		8.0	
		$T_A = 25^\circ\text{C}$	P_D	3.7	W
		$T_A = 100^\circ\text{C}$		1.8	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 3, 4)	Steady State	$T_A = 25^\circ\text{C}$	I_D	11.2	A
Power Dissipation $R_{\theta JA}$ (Notes 1 & 3)	Steady State	$T_A = 25^\circ\text{C}$	P_D	3.7	W
		$T_A = 100^\circ\text{C}$		1.8	
Pulsed Drain Current	$T_A = 25^\circ\text{C}$, $t_p = 10 \mu\text{s}$		I_{DM}	247	A
Current Limited by Package (Note 4)	$T_A = 25^\circ\text{C}$		$I_{DmaxPkg}$	80	A
Operating Junction and Storage Temperature			T_J, T_{stg}	-55 to 175	$^\circ\text{C}$
Source Current (Body Diode)			I_S	60	A
Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^\circ\text{C}$, $V_{DD} = 50 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_{L(pk)} = 31 \text{ A}$, $L = 0.1 \text{ mH}$, $R_G = 25 \Omega$)			E_{AS}	48	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^\circ\text{C}$

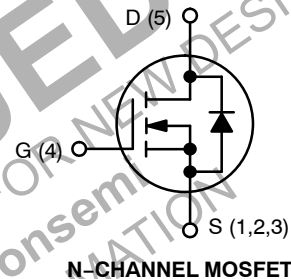
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL RESISTANCE MAXIMUM RATINGS

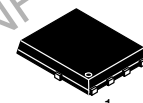
Parameter	Symbol	Value	Unit
Junction-to-Mounting Board (top) – Steady State (Notes 2, 3)	$R_{\psi J-mb}$	1.4	$^\circ\text{C/W}$
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	41	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Psi (Ψ) is used as required per JESD51-12 for packages in which substantially less than 100% of the heat flows to single case surface.

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
60 V	12 mΩ @ 10 V	61 A
	16 mΩ @ 4.5 V	

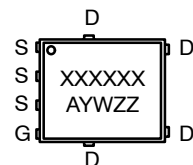


N-CHANNEL MOSFET



DFN5
(SO-8FL)
CASE 488AA
STYLE 1

MARKING DIAGRAM



- A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

NTMFS5844NL, NVMFS5844NL

- Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
- Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			57		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 60 V			1	μA
		T _J = 125°C			100	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	1.5		2.3	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J			6.2		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 10 A		10.2	12	mΩ
		V _{GS} = 4.5 V, I _D = 10 A		13	16	
Forward Transconductance	g _{FS}	V _{DS} = 5 V, I _D = 10 A		27		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 25 V		1460		pF
Output Capacitance	C _{OSS}			150		
Reverse Transfer Capacitance	C _{RSS}			96		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 48 V, I _D = 10 A V _{GS} = 4.5 V, V _{DS} = 48 V, I _D = 10 A		30		nC
Total Gate Charge	Q _{G(TOT)}			15		
Threshold Gate Charge	Q _{G(TH)}			1.0		
Gate-to-Source Charge	Q _{GS}			4.0		
Gate-to-Drain Charge	Q _{GD}			8.0		
Plateau Voltage	V _{GP}			3.0		
Gate Resistance	R _G			0.62		Ω

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 4.5 V, V _{DS} = 48 V, I _D = 10 A, R _G = 2.5 Ω		12		ns
Rise Time	t _r			25		
Turn-Off Delay Time	t _{d(OFF)}			20		
Fall Time	t _f			10		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 10 A	T _J = 25°C		0.79	1.2	V
			T _J = 125°C		0.65		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 10 A			19		ns
Charge Time	t _a				13		
Discharge Time	t _b				6.0		
Reverse Recovery Charge	Q _{RR}				15		nC

- Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

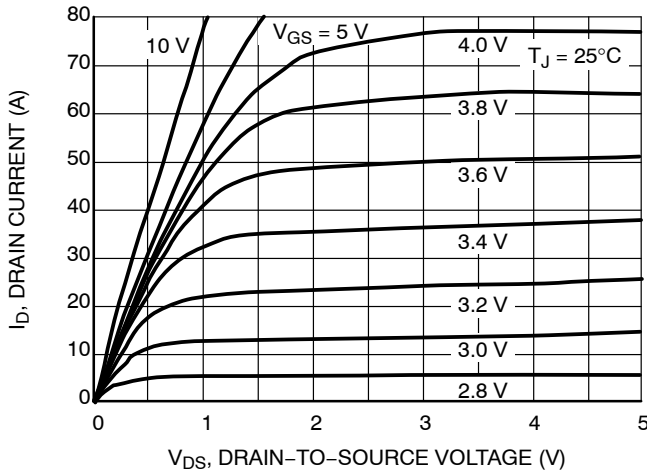


Figure 1. On-Region Characteristics

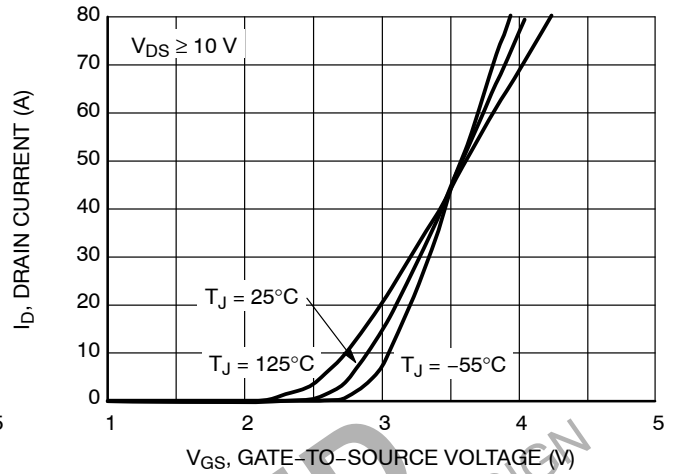


Figure 2. Transfer Characteristics

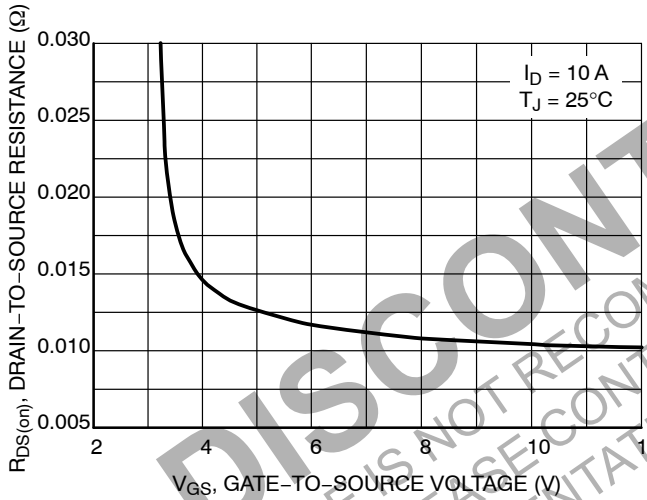


Figure 3. On-Resistance vs. Gate-to-Source Voltage

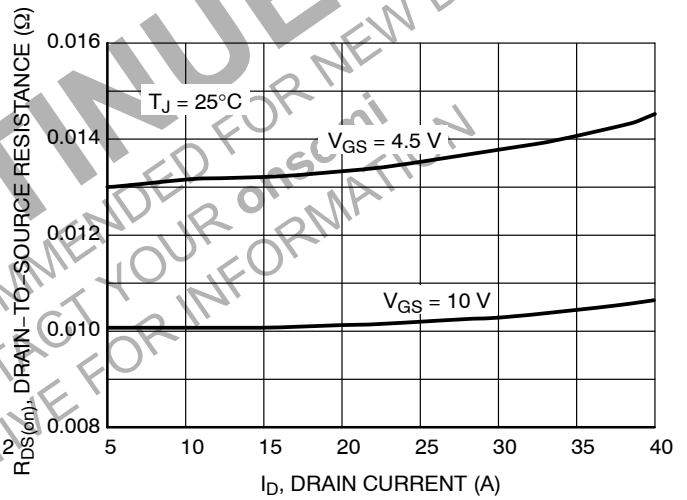


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

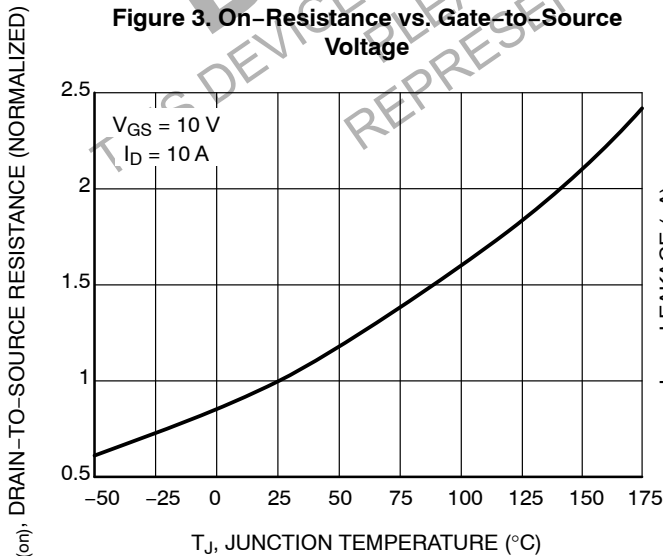


Figure 5. On-Resistance Variation with Temperature

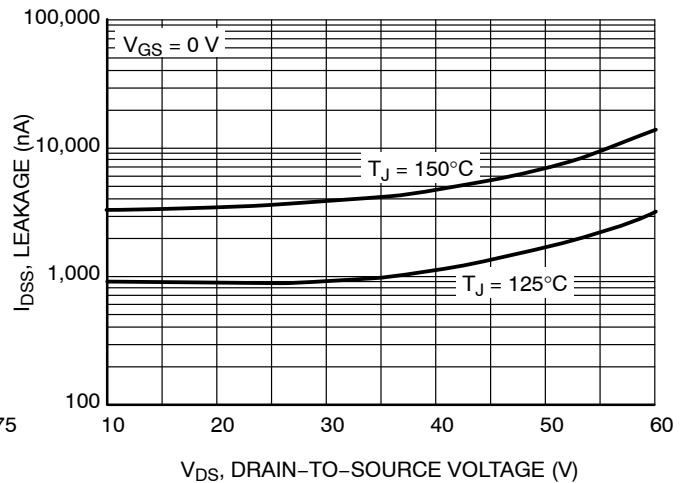


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

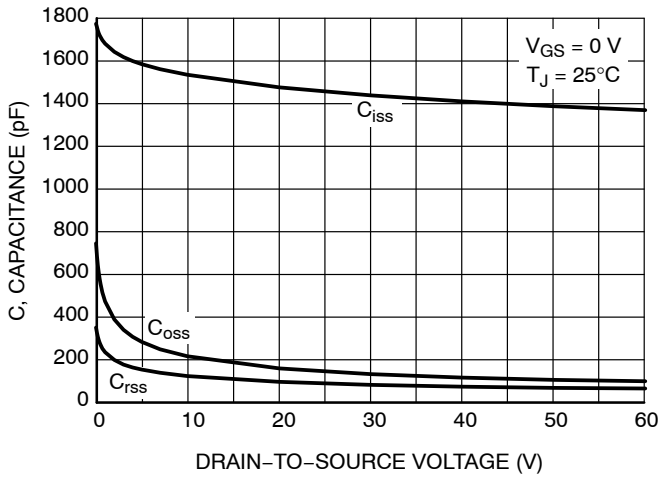


Figure 7. Capacitance Variation

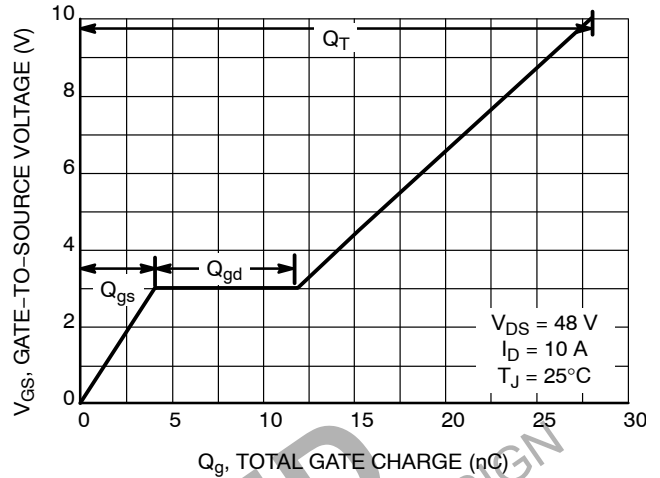


Figure 8. Gate-to-Source Voltage vs. Total Charge

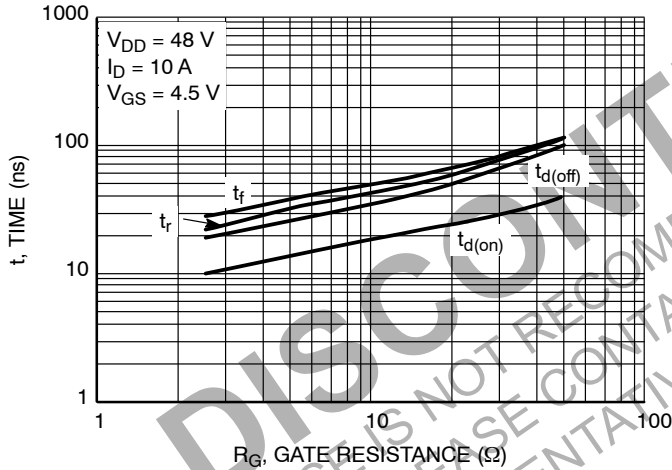


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

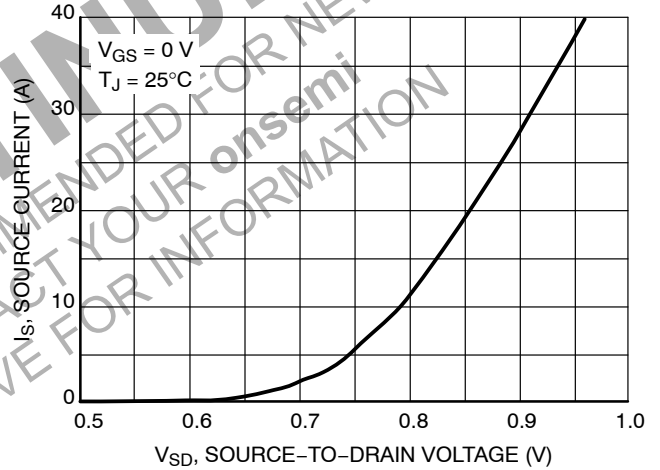


Figure 10. Diode Forward Voltage vs. Current

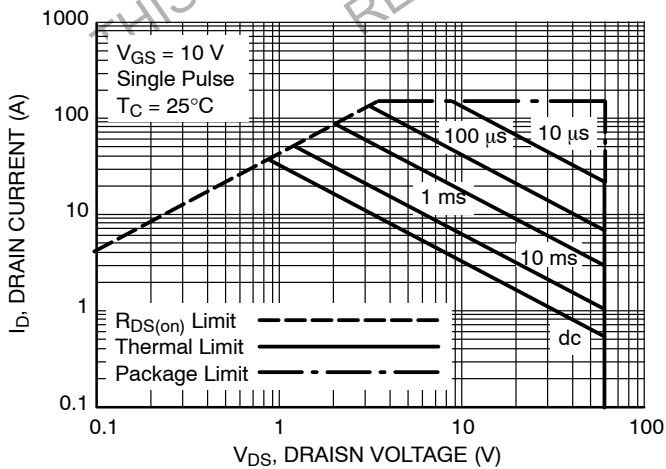


Figure 11. Maximum Rated Forward Biased Safe Operating Area

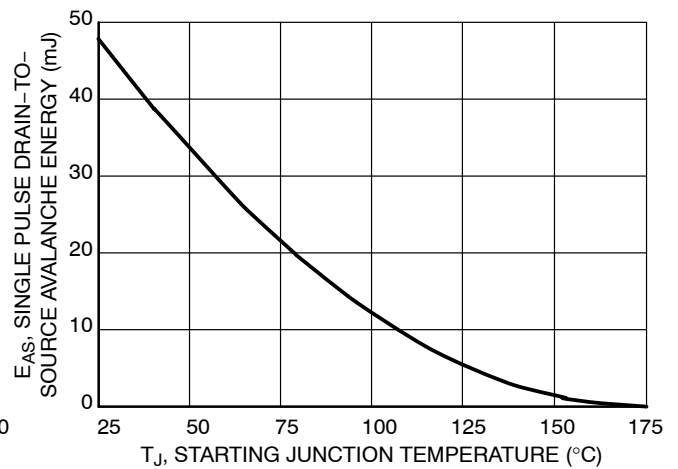


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

TYPICAL CHARACTERISTICS

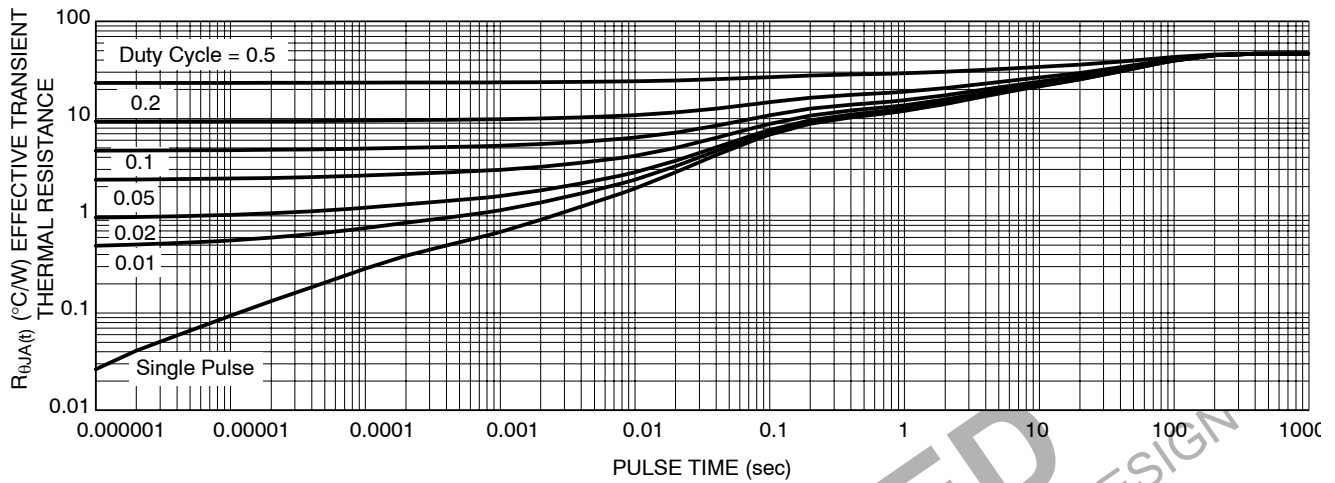


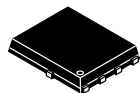
Figure 13. Thermal Response

DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NTMFS5844NLT1G	5844NL	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFS5844NLT1G	V5844L	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFS5844NLWFT1G	5844LW	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFS5844NLT3G	V5844L	DFN5 (Pb-Free)	5000 / Tape & Reel
NVMFS5844NLWFT3G	5844LW	DFN5 (Pb-Free)	5000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

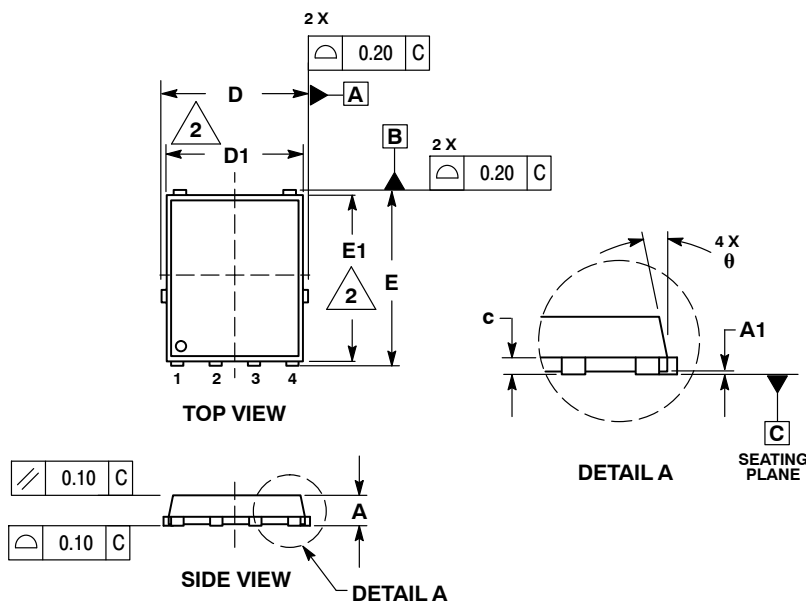
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 2:1

DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE N

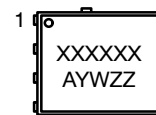
DATE 25 JUN 2018



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

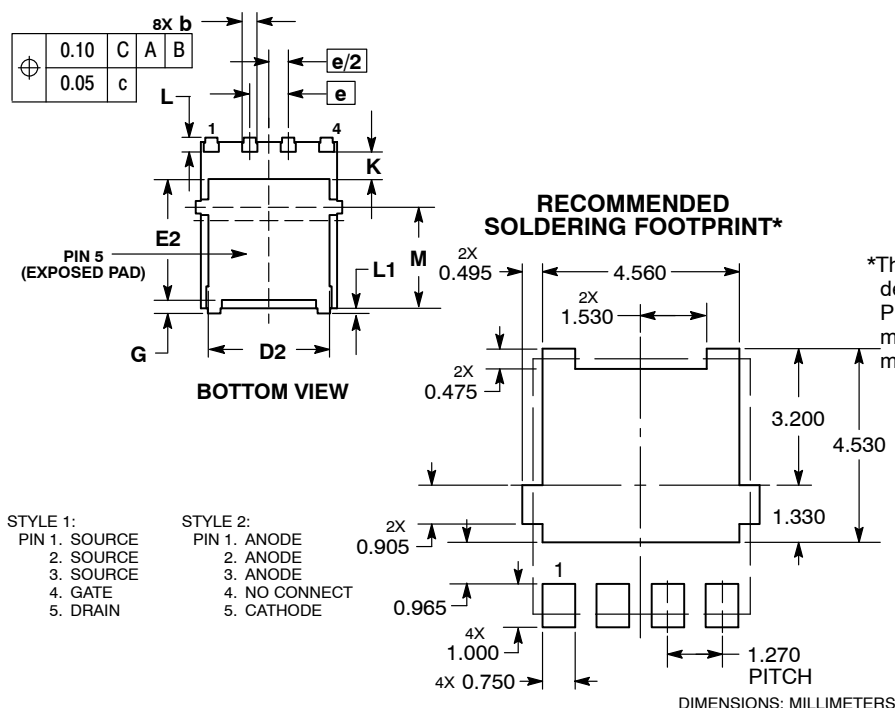
DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0 °	---	12 °

GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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